2N2907A

Switching Transistor

PNP Silicon Epitaxial

Features

- MIL-PRF-19500/291 Qualified
- Available as JAN, JANTX, and JANTXV
- Hermetically Sealed Commercial Product with Option for Military Temperature Range Screening

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	-60	Vdc
Collector - Base Voltage	V _{CBO}	-60	Vdc
Emitter - Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current - Continuous	I _C	-600	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _T	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _T	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit	
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	325	°C/W	
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	150	°C/W	

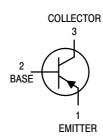
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

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TO-18 CASE 206AA STYLE 1

ORDERING INFORMATION

Device	Package	Shipping
JAN2N2907A		
JANTX2N2907A	TO-18	Bulk
JANTXV2N2907A		

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ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

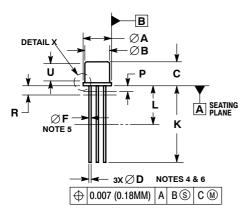
OFF CHARACTERISTICS Collector – Emitter Breakdown Voltage (Note 1) (I _C = −10 mAdc, I _B = 0) V(BR)CEO −60 − Vdc Collector – Base Breakdown Voltage (I _C = −10 µAdc, I _C = 0) V(BR)CBO −5.0 − Vdc Emitter – Base Breakdown Voltage (I _C = −10 µAdc, I _C = 0) V(BR)CBO −5.0 − Vdc Collector Cutoff Current (V _{CE} = −30 Vdc, V _{EB(eff)} = −0.5 Vdc) I _{CEN} − −0.01 µAdc Collector Cutoff Current (V _{CE} = −30 Vdc, I _E = 0) I _{CBO} − −0.01 µAdc Collector Cutoff Current (V _{CE} = −30 Vdc, I _E = 0) I _C = −0.0 I _C = −0.0 µAdc OCOURD Gain (V _{CE} = -30 Vdc, I _E = 0, I _A = 150°C) I _B − −5.0 nAdc DC Current Gain (I _C = −0.1 mAdc, V _{CE} = −10 Vdc) (I _C = −10 Mdc) (I _C = −10 mAdc, V _{CE} = −10 Vdc) (I _C = −10 Mdc) (I _C = −10 mAdc, V _{CE} = −10 Vdc) (I _C = −10 mAdc, V _{CE} = −10 Vdc) (I _C = −10 mAdc, V _{CE} = −10 Vdc) (Note 1) 100 − − −0.4 −0.6 −1.3 −0.4 −0.6 −1.3 −0.4 −0.6 −1.3 −0.4 −0.6 −1.3 −0.4 −0.6 −1.3 −0.6 −1.3	Characteristic			Min	Max	Unit		
	OFF CHARACTERISTICS	OFF CHARACTERISTICS						
	Collector - Emitter Breakdown Voltage	V _{(BR)CEO}	-60	_	Vdc			
	Collector – Base Breakdown Voltage (Ic	V _{(BR)CBO}	-60	-	Vdc			
	Emitter – Base Breakdown Voltage (I _E =	10 μAdc, I _C = 0)	V _{(BR)EBO}	-5.0	_	Vdc		
	Collector Cutoff Current (V _{CE} = −30 Vd	c, V _{EB(off)} = -0.5 Vdc)	I _{CEX}	-	-50	nAdc		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$(V_{CB} = -50 \text{ Vdc}, I_{E} = 0)$	I _{CBO}			μAdc			
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Base Current (V _{CE} = -30 Vdc, V _{EB(off)}	= -0.5 Vdc)	I _B	-	-50	nAdc		
	ON CHARACTERISTICS							
	$(I_{C} = -0.1 \text{ mAdc}, V_{CE} = -10 \text{ Vdc})$ $(I_{C} = -1.0 \text{ mAdc}, V_{CE} = -10 \text{ Vdc})$ $(I_{C} = -10 \text{ mAdc}, V_{CE} = -10 \text{ Vdc})$ $(I_{C} = -150 \text{ mAdc}, V_{CE} = -10 \text{ Vdc})$ (I	h _{FE}	100 100 100	- - - 300 -	-			
	$(I_C = -150 \text{ mAdc}, I_B = -15 \text{ mAdc})$	V _{CE(sat)}			Vdc			
	$(I_C = -150 \text{ mAdc}, I_B = -15 \text{ mAdc})$	V _{BE(sat)}			Vdc			
	SMALL-SIGNAL CHARACTERISTICS	3						
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		f _T	200	_	MHz			
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ h_{fe} $, ($I_C = -20 \text{ mAdc}$, $V_{CE} = -20 \text{ Vdc}$, f		2.0	-	-			
	Output Capacitance (V _{CB} = -10 Vdc, I _E	C _{obo}	-	8.0	pF			
	Input Capacitance (V _{EB} = -2.0 Vdc, I _C	C _{ibo}	-	30	pF			
	SWITCHING CHARACTERISTICS							
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Turn-On Time	,	t _{on}	_	45	ns		
	Delay Time		t _d	-	10	ns		
Storage Time $I_{B1} = I_{B2} = 15 \text{ mAdc}$ (Figure NO TAG) t_s - 80 ns	Rise Time	,	t _r	-	40	ns		
Storage time , t _s - 80 lis	Turn-Off Time	, 33	t _{off}	-	100	ns		
Fall Time t _f - 30 ns	Storage Time	$I_{B1} = I_{B2} = 15 \text{ mAdc}$ (Figure NO TAG)	t _s	_	80	ns		
	Fall Time	t _f	_	30	ns			

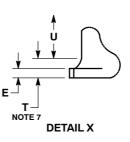
Pulse Test: See section 4 of MIL-STD-750.
 f_T is defined as the frequency at which |h_{fe}| extrapolates to unity.

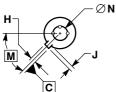
2N2907A

PACKAGE DIMENSIONS

TO-183 CASE 206AA-01 ISSUE O









DETAIL

NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: INCHES.
- DIMENSION J MEASURED FROM DIAMETER A TO EDGE.
 LEAD TRUE POSITION TO BE DETERMINED AT THE GUAGE
- PLANE DEFINED BY DIMENSION R.
 DIMENSION F APPLIES BETWEEN DIMENSION P AND L.
- DIMENSION D APPLIES BETWEEN DIMENSION L AND K. BODY CONTOUR OPTIONAL WITHIN ZONE DEFINED BY DIMEN-
- SIONS A, B, AND T.

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	5.31	5.84	0.209	0.230	
В	4.52	4.95	0.178	0.195	
С	4.32	5.33	0.170	0.210	
D	0.41	0.53	0.016	0.021	
E		0.76		0.030	
F	0.41	0.48	0.016	0.019	
Н	0.91	1.17	0.036	0.046	
J	0.71	1.22	0.028	0.048	
K	12.70	19.05	0.500	0.750	
L	6.35		0.250		
M	45°BSC		45 °BSC		
N	2.54	2.54 BSC		0.100 BSC	
P		1.27		0.050	
R	1.37 BSC		0.054 BSC		
T		0.76		0.030	
U	2.54		0.100		

STYLE 1:

PIN 1. EMITTER

BASE

COLLECTOR

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